

**KS54AHCT 533  
KS74AHCT****Octal D-Type Transparent Latches  
with 3-State Outputs T-46-07-05****FEATURES**

- 8 latches in a single package
- Full parallel access for loading
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ( $I_{OL} = 24 \text{ mA}$  @  $V_{OL} = 0.5\text{V}$ ) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:  
KS74AHCT:  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$   
KS54AHCT:  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

**DESCRIPTION**

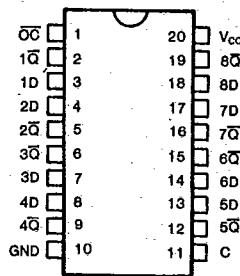
The '533 consists of 8 high-speed D-type latches coupled to 3-state output buffers with high drive current capability. It can be used in implementing buffer registers, I/O ports, bidirectional bus drivers and working registers.

The latches are transparent: when the enable (C) is high, the  $\bar{Q}$  outputs follow the complements of the data (D) inputs. When the enable is low, the outputs latch at the levels that were set up at the D inputs.

The output buffers are controlled by a common signal ( $\bar{OC}$ ) which places the outputs at high-impedance state when it is taken high. The OC signal does not affect the internal operations of the latches. Old data can be retained or new data can be entered while outputs are off.

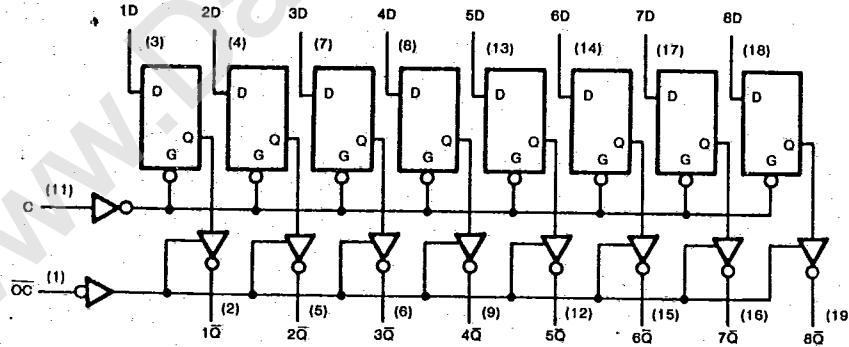
These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to Vcc and ground.

**PIN CONFIGURATION****FUNCTION TABLE**

(Each Latch)

Inputs	Output		
$\bar{OC}$	Enable C	D	$\bar{Q}$
L	H	H	L
L	H	L	H
L	L	X	$\bar{Q}_0$
H	X	X	Z

**LOGIC DIAGRAM**

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KS54AHCT 533  
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with 3-State Outputs T-46-07-05**Absolute Maximum Ratings\***

Supply Voltage Range V <sub>CC</sub> , . . . . .	-0.5V to +7V
DC Input Diode Current, I <sub>IK</sub> (V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> +0.5V) . . . . .	±20 mA
DC Output Diode Current, I <sub>OK</sub> (V <sub>O</sub> < -0.5V or V <sub>O</sub> > V <sub>CC</sub> +0.5V) . . . . .	±20 mA
Continuous Output Current Per Pin, I <sub>O</sub> (-0.5V < V <sub>O</sub> < V <sub>CC</sub> +0.5V) . . . . .	±70 mA
Continuous Current Through V <sub>CC</sub> or GND pins . . . . .	±250 mA
Storage Temperature Range, T <sub>STG</sub> . . . . .	-65°C to +150°C
Power Dissipation Per Package, P <sub>D†</sub> . . . . .	500 mW

- \* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:  
Plastic Package (N): -12mW/°C from 65°C to 85°C  
Ceramic Package (J): -12mW/°C from 100°C to 125°C

**Recommended Operating Conditions**

Supply Voltage, V <sub>CC</sub> . . . . .	4.5V to 5.5V
DC Input & Output Voltages*, V <sub>IN</sub> , V <sub>OUT</sub> . . . . .	0V to V <sub>CC</sub>
Operating Temperature Range	KS74AHCT: -40°C to +85°C KS54AHCT: -55°C to +125°C
Input Rise & Fall Times, t <sub>R</sub> , t <sub>F</sub> . . . . .	Max 500 ns

\* Unused inputs must always be tied to an appropriate logic voltage level (either V<sub>CC</sub> or GND)

**DC ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub>=5V±10% Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T <sub>A</sub> = 25°C		KS74AHCT T <sub>A</sub> = -40°C to +85°C	KS54AHCT T <sub>A</sub> = -55°C to +125°C	Unit
			Typ	Guaranteed Limits			
Minimum High-Level Input Voltage	V <sub>IH</sub>			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V <sub>IL</sub>			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =-20μA I <sub>O</sub> =-6mA	V <sub>CC</sub> 4.2	V <sub>CC</sub> -0.1 3.98	V <sub>CC</sub> -0.1 3.84	V <sub>CC</sub> -0.1 3.7	V
Maximum Low-Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =20μA I <sub>O</sub> =12mA I <sub>O</sub> =24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I <sub>IN</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND		±0.1	±1.0	±1.0	μA
Maximum 3-State Leakage Current	I <sub>OZ</sub>	Output Enable =V <sub>IH</sub> V <sub>OUT</sub> =V <sub>CC</sub> or GND		±0.6	±5.0	±10.0	μA
Maximum Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI <sub>CC</sub>	per input pin V <sub>I</sub> =2.4V other Inputs: at V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA		2.7	2.9	3.0	mA



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## AC ELECTRICAL CHARACTERISTICS (Input tr, tf&lt;2 ns), AHCT533

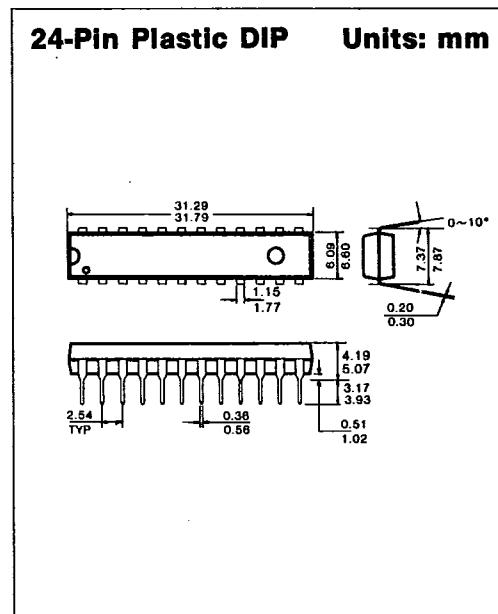
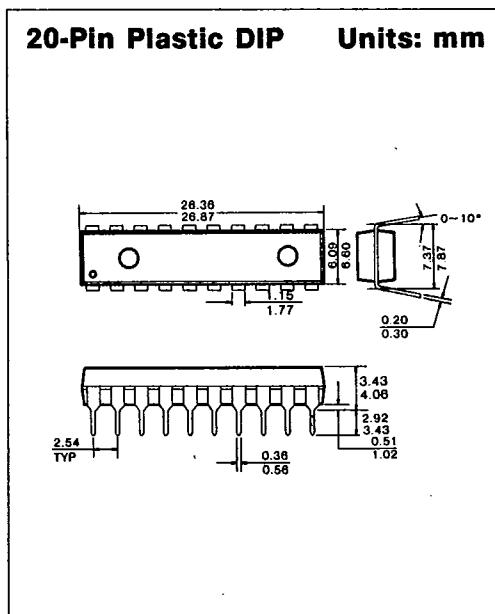
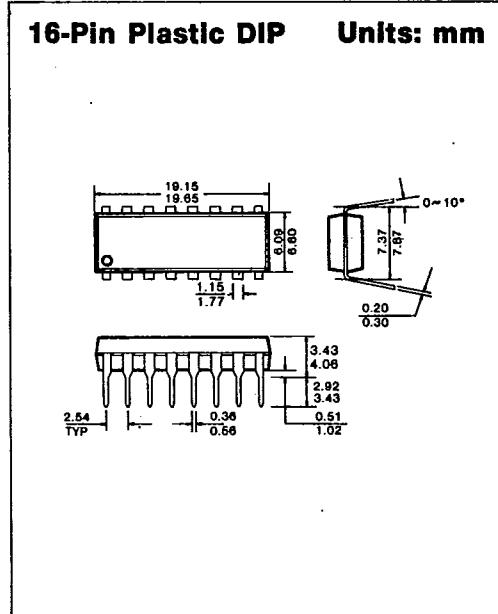
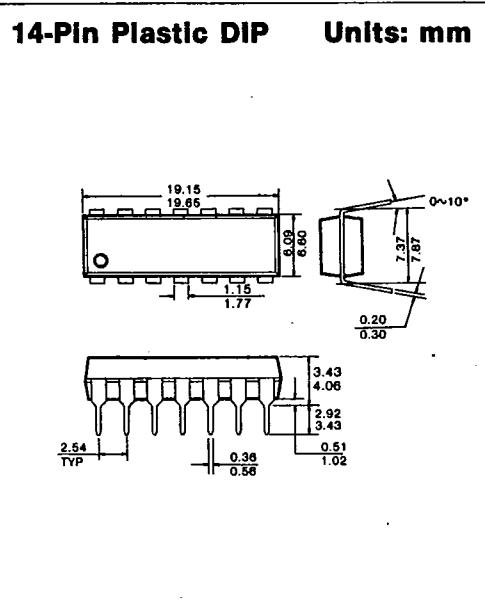
Characteristic	Symbol	Conditions <sup>†</sup>	T <sub>a</sub> = 25°C V <sub>cc</sub> = 5.0V	KS74AHCT T <sub>a</sub> = -40°C to +85°C V <sub>cc</sub> = 5.0V ± 10%		KS54AHCT T <sub>a</sub> = -55°C to +125°C V <sub>cc</sub> = 5.0V ± 10%		Unit
			Typ	Min	Max	Min	Max	
Propagation Delay, D to $\bar{Q}$	t <sub>PLH</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	10 13		16 21		19 25	ns
	t <sub>PHL</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	10 13		16 21		19 25	
Propagation Delay, C to Q	t <sub>PLH</sub>	C = 50pF C <sub>L</sub> = 150pF	13 16		21 26		25 31	ns
	t <sub>PHL</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	13 16		21 26		25 31	
Output Enable Time, $\bar{OC}$ to any $\bar{Q}$	t <sub>PZH</sub>	R <sub>L</sub> = 1kΩ	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	11 14	18 23		22 28	ns
	t <sub>PZL</sub>	R <sub>L</sub> = 1kΩ	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	11 14	18 23		22 28	
Output Disable Time, $\bar{OC}$ to any $\bar{Q}$	t <sub>PHZ</sub>	R <sub>L</sub> = 1kΩ		13	18		22	ns
	t <sub>PLZ</sub>	C <sub>L</sub> = 50pF		13	18		22	
Pulse Width, C High	tw			9	15		18	ns
Setup Time, D before C↓	t <sub>su</sub>			9	15		18	ns
Hold Time, D after C↓	t <sub>h</sub>			3	5		7	ns
Input Capacitance	C <sub>iN</sub>			5				pF
Output Capacitance	C <sub>out</sub>	Output Disabled		10				pF
Power Dissipation Capacitance* (per stage)	C <sub>PD</sub>	$\bar{OC} = V_{cc}$ $OC = GND$		5 30				pF

\* C<sub>PD</sub> determines the no-load dynamic power dissipation: P<sub>D</sub> = C<sub>PD</sub> V<sub>cc</sub><sup>2</sup> f + I<sub>cc</sub> V<sub>cc</sub>.

† For AC switching test circuits and timing waveforms see section 2.



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**PACKAGE DIMENSIONS**T-90-20**1. PLASTIC PACKAGES**

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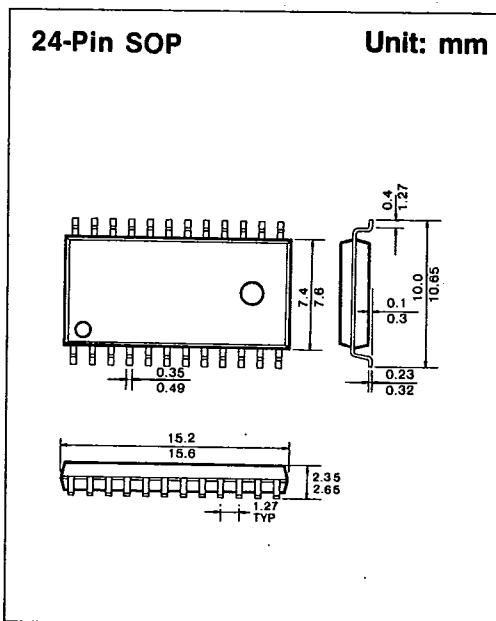
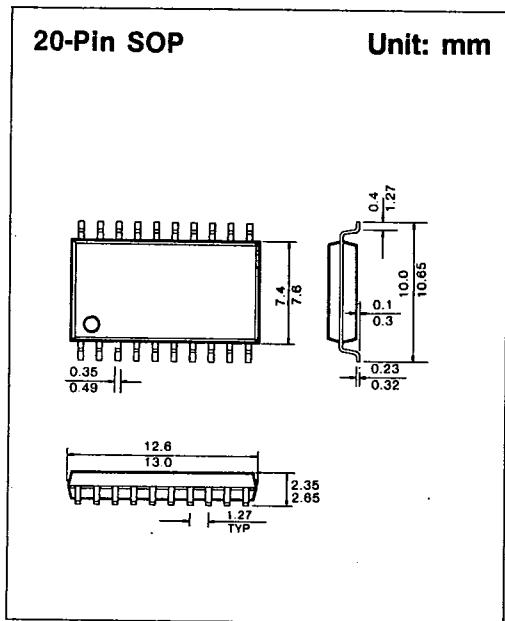
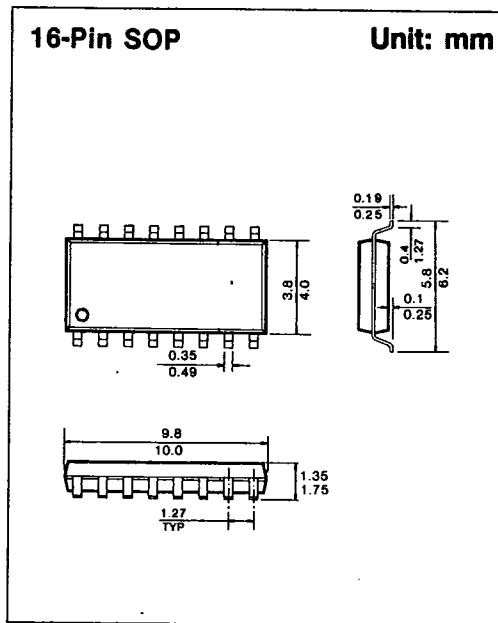
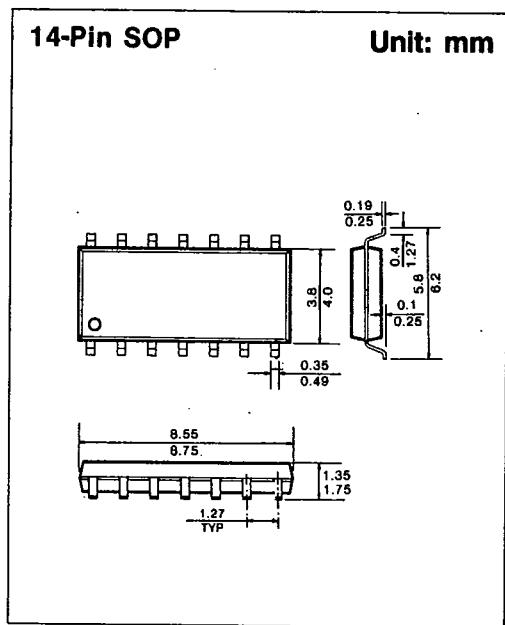


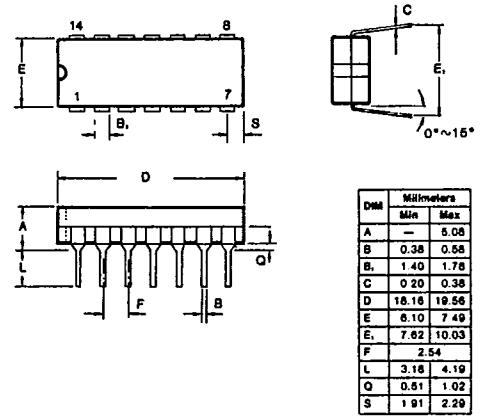
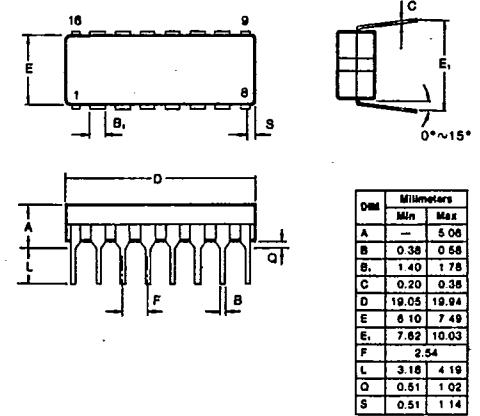
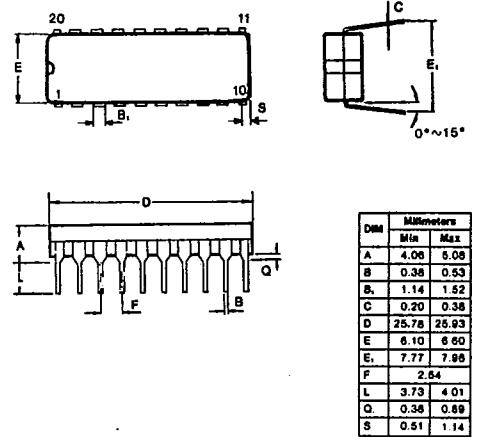
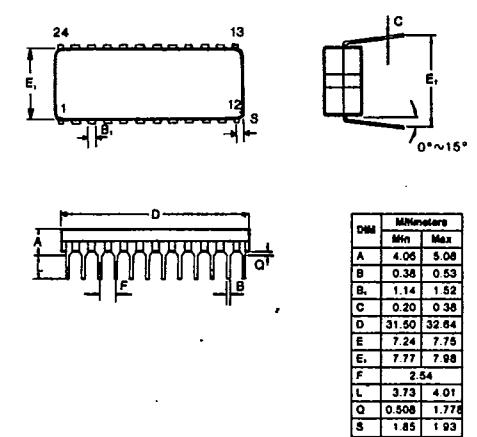
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A-04

781

**PACKAGE DIMENSIONS****T-90-20****SAMSUNG SEMICONDUCTOR****1676****A-05****782**

**PACKAGE DIMENSIONS**T-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

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